



Heterogeneous Integration Roadmap Workshop

MobileTWG

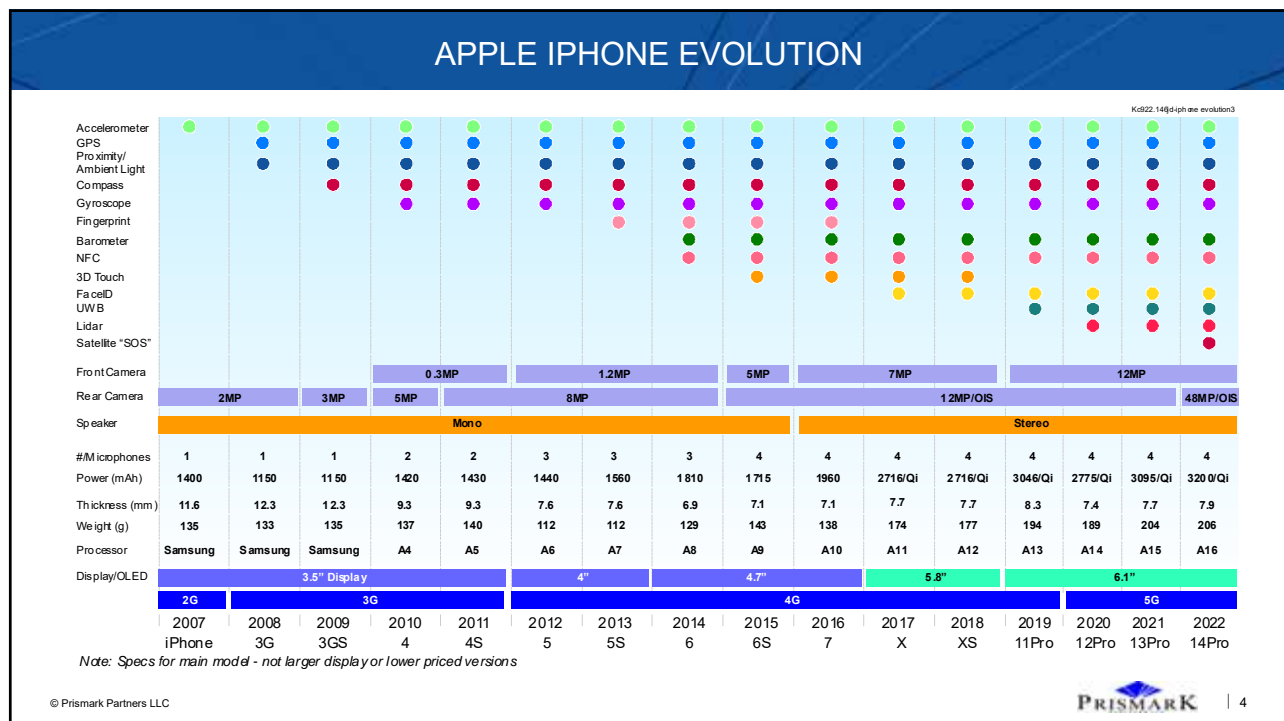
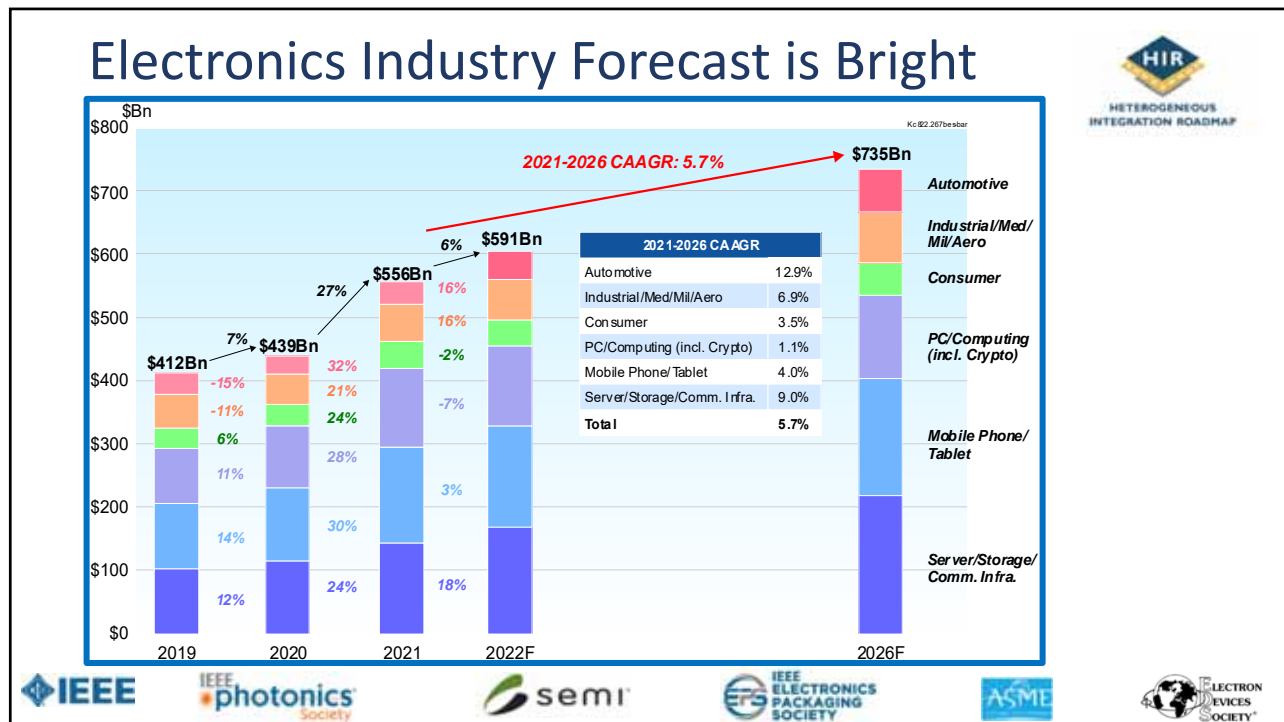
TWG Chair & Co-Chair
William (Bill) Chen & Benson Chan



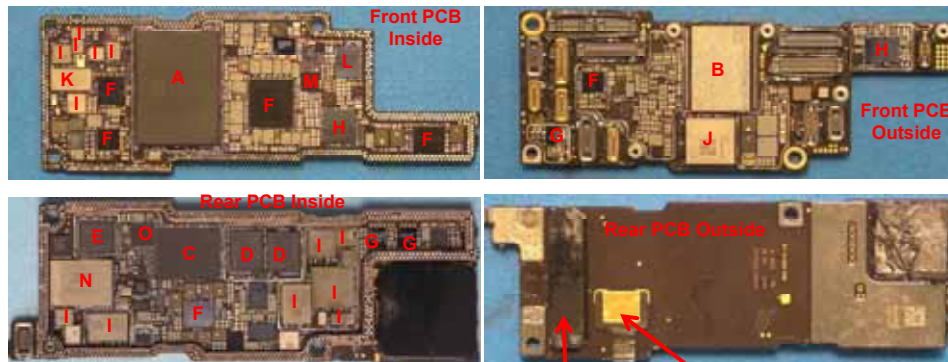
Agenda

- Mobile is essential tool for consumers for daily lives
- Smart Phone growth in capabilities & features
- 5G mmWave a technology disruption
- Battery
- Collaboration across Technical Working Groups
- Summary





APPLE IPHONE 14 PRO MAIN BOARD ASSEMBLY



Photos source: Prismark/Binghamton University

- | | |
|---|-----------------------------------|
| A. Apple A16 Applications Processor | H. Apple/Cirrus Logic Audio Codec |
| B. Flash Memory | I. FEM (Broadcom, Skyworks, etc.) |
| C. Qualcomm SDX65M 2G-5G Baseband | J. Wi-Fi Module |
| D. Qualcomm SDR735 2G-5G TRx (sub-6GHz), 2x | K. USI UWB Module |
| E. Qualcomm SMR546 5G IF TRx (mmWave) | L. Broadcom Wireless Charging |
| F. Power Manger (Apple, Qualcomm, etc) | M. NXP Display Manager |
| G. Apple/Cirrus Logic Audio Amplifier | N. 5G mmWave Module |
| | O. NXP NFC Controller |

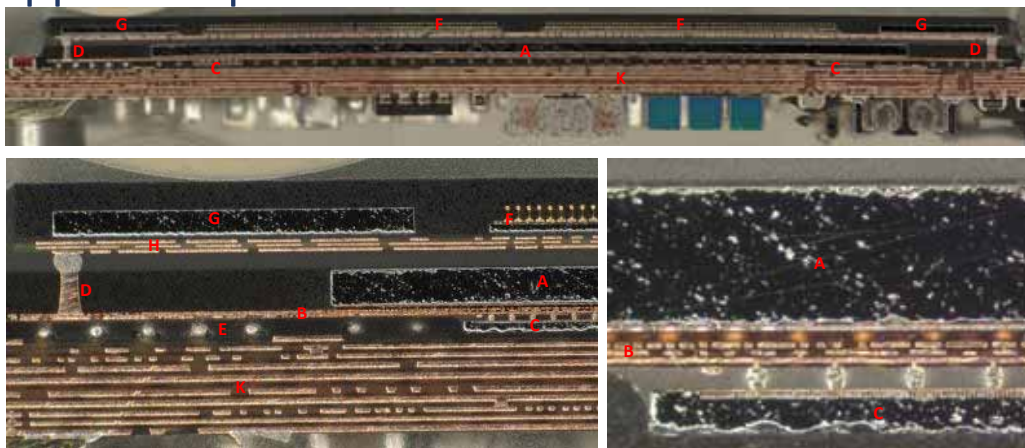
Note: Front board is 10L any-layer HDI, rear board is 8L any-layer HDI

© Prismark Partners LLC

PRISMARK

| 5

Apple A16 processor



- A16 in FOWLP (A) as bottom package
- 5 RDL layers (B)
- Capacitor die (C) on underside of FOWLP
- Peripheral TMV (D) for top package interconnect
- 0.3mm ball pitch (E)
- 0.4mm collapsed height

- 0.9mm total collapsed height
- 10L Anylayer digital main board (K)

- Memory (F) and dummy die (G) in top package
- Wirebonded memory die
- 3L HDI (H)
- 0.3mm ball pitch (not shown)
- 0.5mm collapsed height

Photos source: Prismark/Binghamton University

Smart Phones Lead in SiP Implementation



Apple A12 Processor



WLP Fan-Out Apple

Samsung EXYNOS 9810



Advanced PoP
Samsung

Huawei HiSilicon Kirin 980

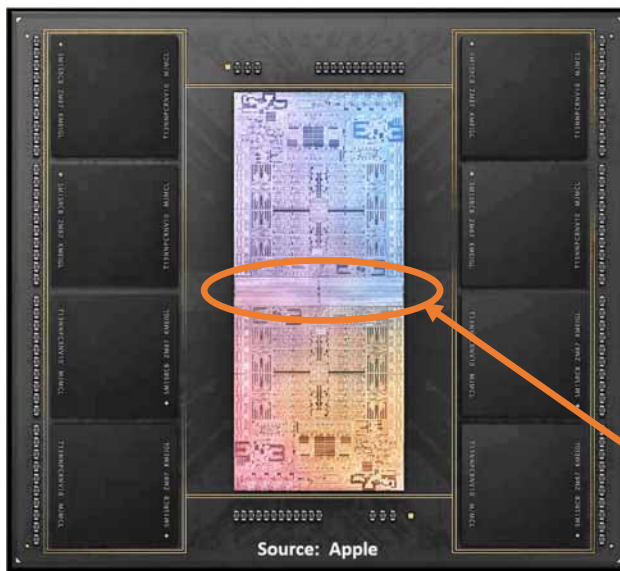


Advanced PoP
Huawei

Source: Prismark Partners & Binghamton University



Apple Mac Studio Ultra



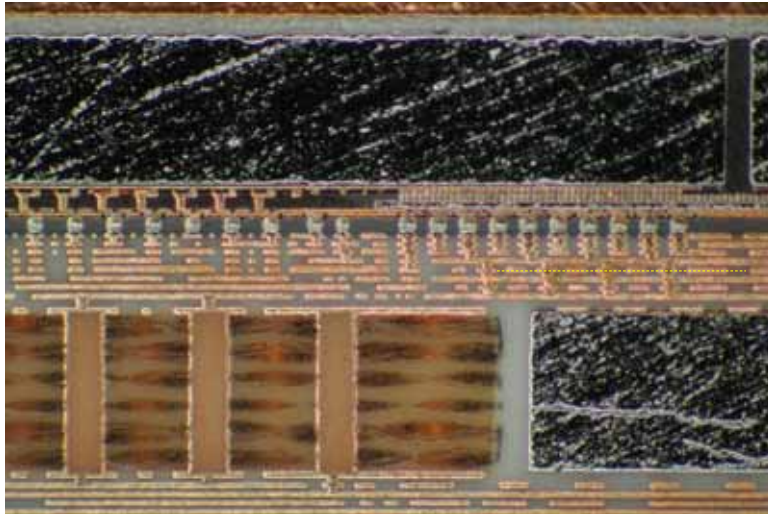
Source: Apple



Silicon bridge
connection

70mm Package

Joining metallurgy between Apple Ultra M1 logic chip and Si bridge



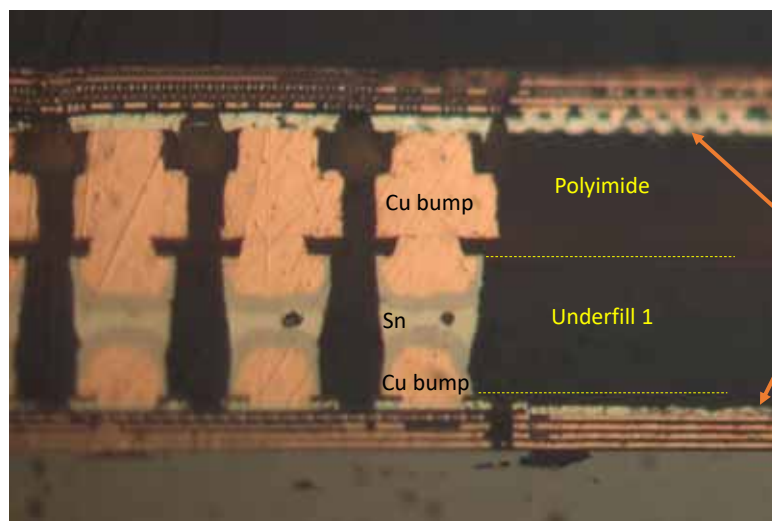
M1 chip circuits

Si bridge circuits

Core Substrate w/
embedded device

Photos source: Prismark/Binghamton University

Joining metallurgy between Apple Ultra M1 logic chip and Si bridge



M1 chip circuits

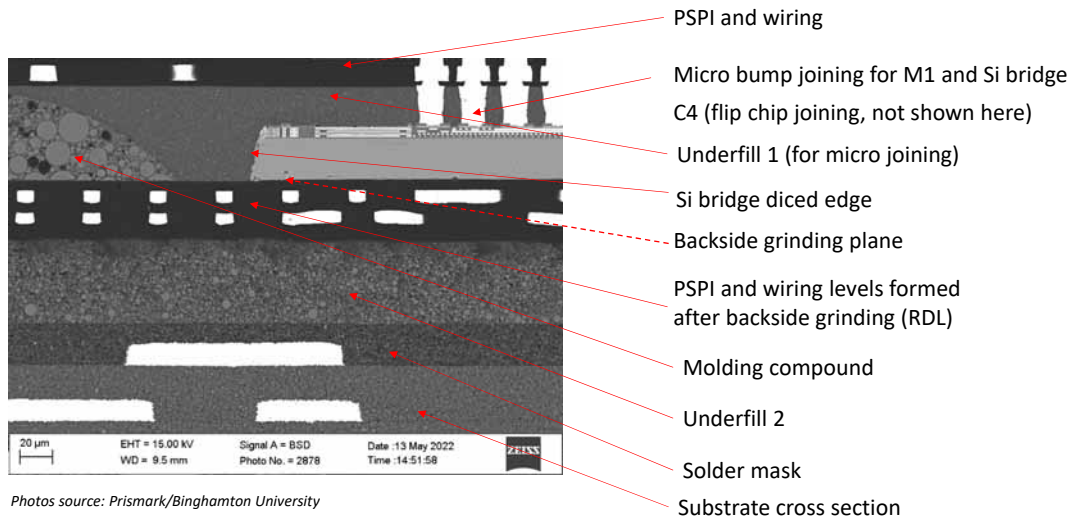
25 micron pitch

Aluminum final metallization

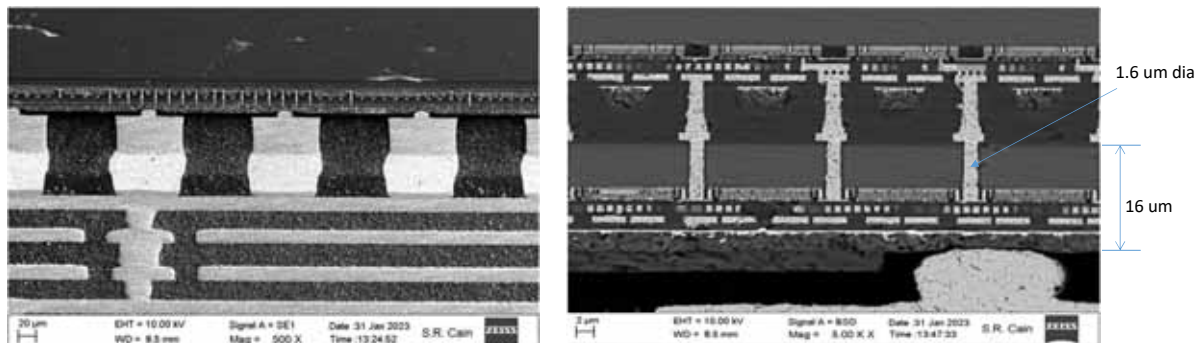
Si bridge circuits

Photos source: Prismark/Binghamton University

A cross section of Si Bridge and substrate Interface

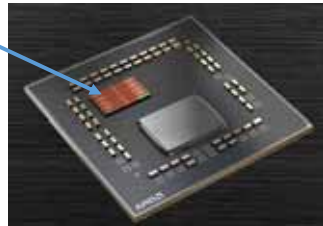


Die Stacking in AMD Ryzen 7 5800X3D



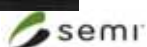
Source: Binghamton University & Prismark Partners

Stacked L3 cache



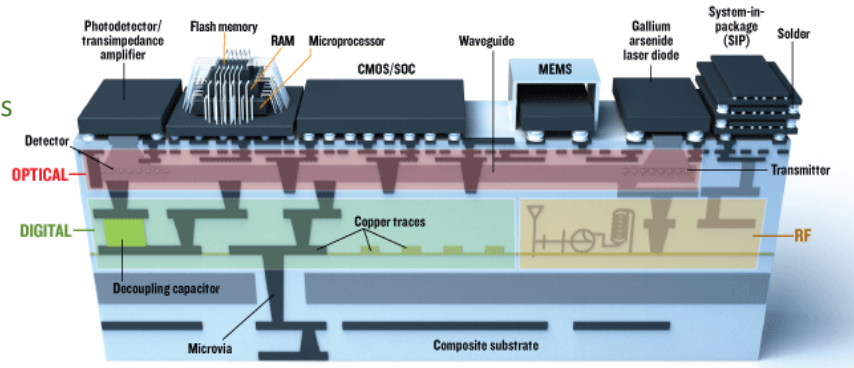
Die to die interconnect: ~1.6 μm dia columns on 15.5 μm pitch

Source: AMD



SOLUTION

- Smaller nodes
- 2.5 & 3D
- Smaller interconnects
- Smaller Line/space
- Shorter distances
- TSV & Bridges
- Embedded
- Co-packaging

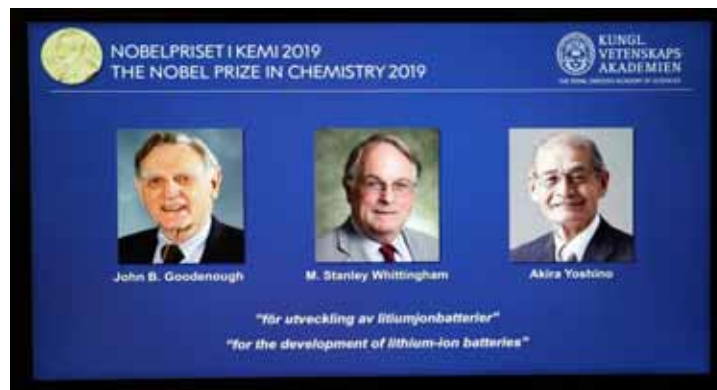


Press Release October 9th, 2019

[The Royal Swedish Academy of Sciences](#)

awards the Nobel Prize in Chemistry 2019 to

- **John B. Goodenough**
The University of Texas at Austin, USA
- **M. Stanley Whittingham**
Binghamton University, State University of New York, USA
- **Akira Yoshino**
Asahi Kasei Corporation, Tokyo,
JapanMeijo University, Nagoya, Japan
“for the development of lithium-ion batteries”



“They created a rechargeable world”

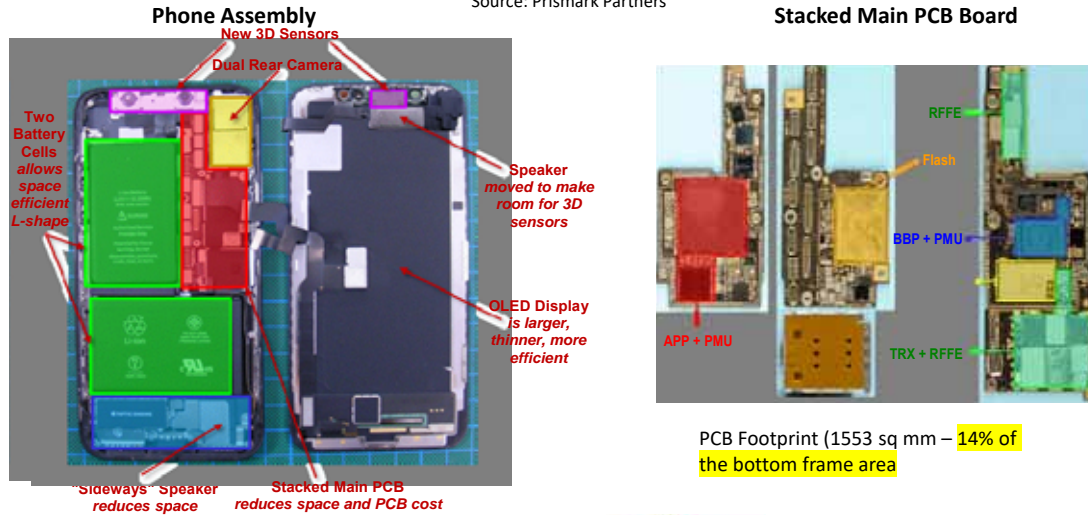
The Nobel Prize in Chemistry 2019 rewards the development of the lithium-ion battery. This lightweight, rechargeable and powerful battery is now used in everything from mobile phones to laptops and electric vehicles. It can also store significant amounts of energy from solar and wind power, making possible a fossil fuel-free society. Press Release October 9th, 2019

[The Royal Swedish Academy of Sciences](#)

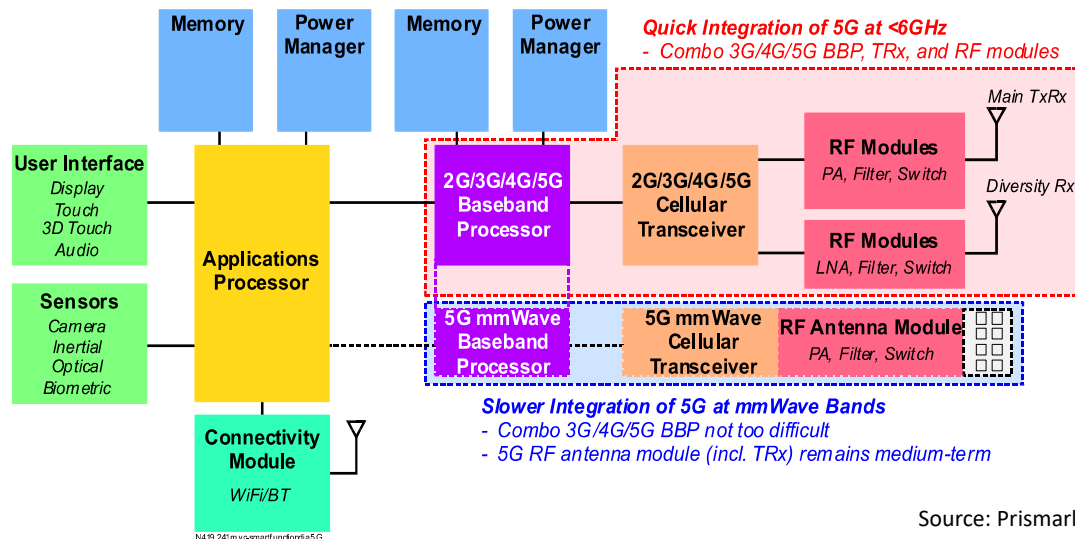


How much space does the battery occupy? Example from Apple iPhone X

Source: Prismark Partners



Impact of 5G on Packaging

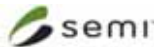


Source: Prismark



TWGs Collaboration

MEMS & Sensor Integration
5G & 6G
Supply Chain
SIP & Module
Emerging Materials
Single & Multichip Integration
Reliability
Additive Manufacturing



Low warpage Low Dielectric -ABF

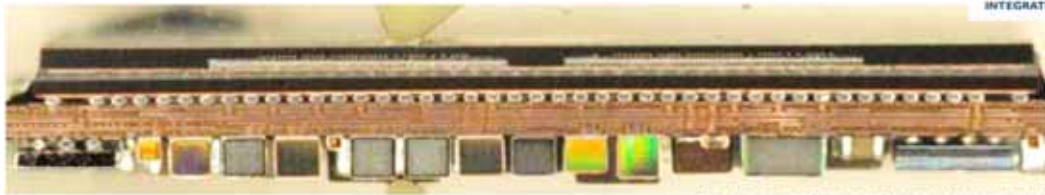
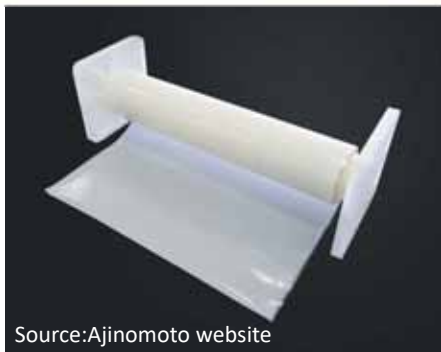
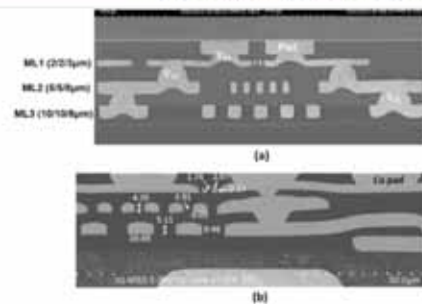


Photo source: Prismark/Binghamton University

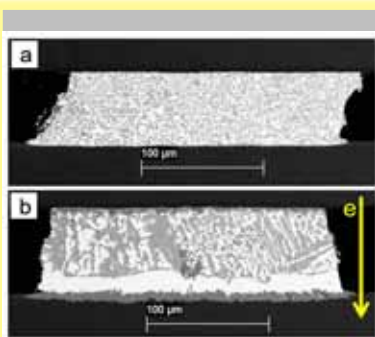


Source: Ajinomoto website



G.C.F Chen et al., "2.3D Hybrid substrate with Ajinomoto build-up film for Heterogenous Integration" May 2022, pp 30-37 (Unimicron)

ELECTROMIGRATION



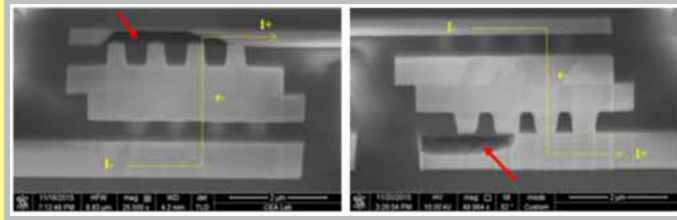
EM behavior of Bi-Sn solder as potential lower process temp material.

Source: E. Cotts, BU

EM is Major concern

- Joule heating and hot spot due to thin layers
- higher current density
- Software and physics based models are used to predict and mitigate Void formation

Source: P. Ho (UT)



EXTREME THIN DIES

Carrier bonding
Thinning
CMP-TSV reveal
TCB (thermal compression bonding)
Bonding)
Debond/Lift off

Reference: Julien Bertheau, et al (imec) & Atsushi Nakamura (Fujifilm Electronic Materials), "Extreme Thinned-Wafer Bonding Using Low Temperature Curable Polyimide for Advanced Wafer Level Integrations" in IEEE 68th Electronic Components and Technology Conference, San Diego

